

Type Designator: BLY10

Material of Transistor: Si

Polarity: NPN

Maximum Collector Power Dissipation ( $P_c$ ): 10 W

Maximum Collector-Base Voltage  $|V_{cb}|$ : 20 V

Maximum Collector-Emitter Voltage  $|V_{ce}|$ : 20 V

Maximum Emitter-Base Voltage  $|V_{eb}|$ : 6 V

Maximum Collector Current  $|I_c \text{ max}|$ : 0.5 A

Max. Operating Junction Temperature ( $T_j$ ): 200 °C

Transition Frequency ( $f_t$ ): 50 MHz

Collector Capacitance ( $C_c$ ): 48 pF

Forward Current Transfer Ratio ( $h_{FE}$ ), MIN: 12

Noise Figure, dB: -

Package: TO3